

ABSTRACT OF THE DISCLOSURE

A reading circuit, for reading data from one memory cell of a plurality of memory cells, includes a plurality of division sensing circuits each connected to the one memory cell via a sensing line corresponding thereto among a plurality of sensing lines; and a current-voltage conversion circuit for converting a current flowing through each sensing line into a sensing voltage representing a potential of the corresponding sensing line. Each division sensing circuit includes a current load circuit for supplying a current to the one memory cell via a corresponding sensing line, and a sense amplifier for sensing a potential difference between the corresponding sensing line and a corresponding reference line of a plurality of reference lines. The current load circuit included in at least one division sensing circuit has a current supply capability different from that of the current load circuit included in another division sensing circuits.